

## OptiMOS® -P2 Power-Transistor



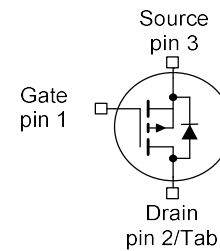
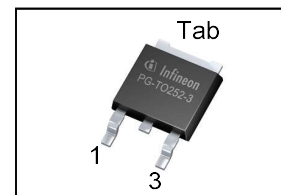
### Features

- P-channel - Normal Level - Enhancement mode
- AEC qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- RoHS compliant
- 100% Avalanche tested

### Product Summary

|              |     |    |
|--------------|-----|----|
| $V_{DS}$     | -30 | V  |
| $R_{DS(on)}$ | 4.5 | mΩ |
| $I_D$        | -90 | A  |

PG-TO252-3-11



| Type          | Package       | Marking |
|---------------|---------------|---------|
| IPD90P03P4-04 | PG-TO252-3-11 | 4P0304  |

**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                              | Symbol         | Conditions                                          | Value        | Unit |
|----------------------------------------|----------------|-----------------------------------------------------|--------------|------|
| Continuous drain current <sup>1)</sup> | $I_D$          | $T_C=25\text{ °C}$ ,<br>$V_{GS}=-10\text{ V}$       | -90          | A    |
|                                        |                | $T_C=100\text{ °C}$ ,<br>$V_{GS}=-10\text{ V}^{2)}$ | -90          |      |
| Pulsed drain current <sup>2)</sup>     | $I_{D,pulse}$  | $T_C=25\text{ °C}$                                  | -360         |      |
| Avalanche energy, single pulse         | $E_{AS}$       | $I_D=-45\text{ A}$                                  | 370          | mJ   |
| Avalanche current, single pulse        | $I_{AS}$       | -                                                   | -90          | A    |
| Gate source voltage                    | $V_{GS}$       | -                                                   | ±20          | V    |
| Power dissipation                      | $P_{tot}$      | $T_C=25\text{ °C}$                                  | 137          | W    |
| Operating and storage temperature      | $T_j, T_{stg}$ | -                                                   | -55 ... +175 | °C   |
| IEC climatic category; DIN IEC 68-1    | -              | -                                                   | 55/175/56    |      |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

### Thermal characteristics<sup>2)</sup>

|                                     |            |                                              |   |   |     |     |
|-------------------------------------|------------|----------------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case | $R_{thJC}$ | -                                            | - | - | 1.1 | K/W |
| SMD version, device on PCB          | $R_{thJA}$ | minimal footprint                            | - | - | 62  |     |
|                                     |            | 6 cm <sup>2</sup> cooling area <sup>3)</sup> | - | - | 40  |     |

### Electrical characteristics, at $T_j=25^\circ\text{C}$ , unless otherwise specified

#### Static characteristics

|                                  |               |                                                      |      |       |      |            |
|----------------------------------|---------------|------------------------------------------------------|------|-------|------|------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0V, I_D=-1mA$                                | -30  | -     | -    | V          |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=-253\mu A$                       | -2.0 | -3.0  | -4.0 |            |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=-24V, V_{GS}=0V, T_j=25^\circ\text{C}$       | -    | -0.05 | -1   | $\mu A$    |
|                                  |               | $V_{DS}=-24V, V_{GS}=0V, T_j=125^\circ\text{C}^{2)}$ | -    | -20   | -200 |            |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=-20V, V_{DS}=0V$                             | -    | -     | -100 | nA         |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=-10V, I_D=-90A$                              | -    | 3.6   | 4.5  | m $\Omega$ |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

### Dynamic characteristics<sup>2)</sup>

|                              |              |                                                               |   |      |       |    |
|------------------------------|--------------|---------------------------------------------------------------|---|------|-------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0V, V_{DS}=-25V,$<br>$f=1MHz$                         | - | 7900 | 10300 | pF |
| Output capacitance           | $C_{oss}$    |                                                               | - | 2340 | 3040  |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                               | - | 83   | 166   |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=-15V,$<br>$V_{GS}=-10V, I_D=-90A,$<br>$R_G=3.5\Omega$ | - | 35   | -     | ns |
| Rise time                    | $t_r$        |                                                               | - | 10   | -     |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                               | - | 70   | -     |    |
| Fall time                    | $t_f$        |                                                               | - | 20   | -     |    |

### Gate Charge Characteristics<sup>2)</sup>

|                       |               |                                                         |   |      |     |    |
|-----------------------|---------------|---------------------------------------------------------|---|------|-----|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=-24V, I_D=-90A,$<br>$V_{GS}=0 \text{ to } -10V$ | - | 42   | 55  | nC |
| Gate to drain charge  | $Q_{gd}$      |                                                         | - | 10   | 20  |    |
| Gate charge total     | $Q_g$         |                                                         | - | 100  | 130 |    |
| Gate plateau voltage  | $V_{plateau}$ |                                                         | - | -5.3 | -   | V  |

### Reverse Diode

|                                                |               |                                                |   |    |      |    |
|------------------------------------------------|---------------|------------------------------------------------|---|----|------|----|
| Diode continuous forward current <sup>2)</sup> | $I_S$         | $T_C=25^\circ C$                               | - | -  | -90  | A  |
| Diode pulse current <sup>2)</sup>              | $I_{S,pulse}$ |                                                | - | -  | -360 |    |
| Diode forward voltage                          | $V_{SD}$      | $V_{GS}=0V, I_F=-90A,$<br>$T_j=25^\circ C$     | - | -  | -1.3 | V  |
| Reverse recovery time <sup>2)</sup>            | $t_{rr}$      | $V_R=-15V, I_F=-50A,$<br>$di_F/dt=-100A/\mu s$ | - | 50 | -    | ns |
| Reverse recovery charge <sup>2)</sup>          | $Q_{rr}$      |                                                | - | 70 | -    | nC |

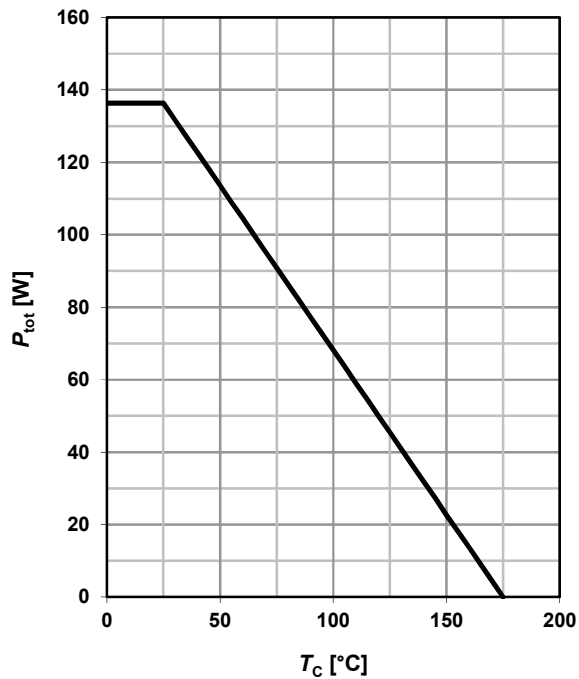
<sup>1)</sup> Current is limited by bondwire; with an  $R_{thJC} = 1.1K/W$  the chip is able to carry -143A at 25°C.

<sup>2)</sup> Defined by design. Not subject to production test.

<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

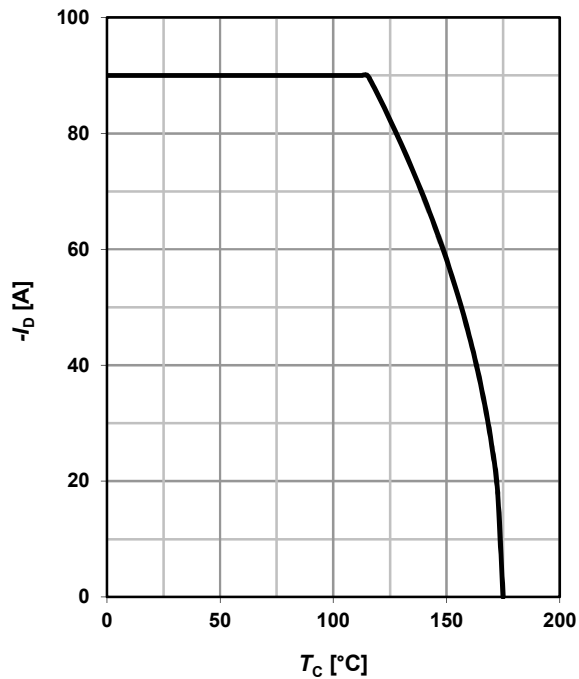
### 1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \leq -6\text{V}$$



### 2 Drain current

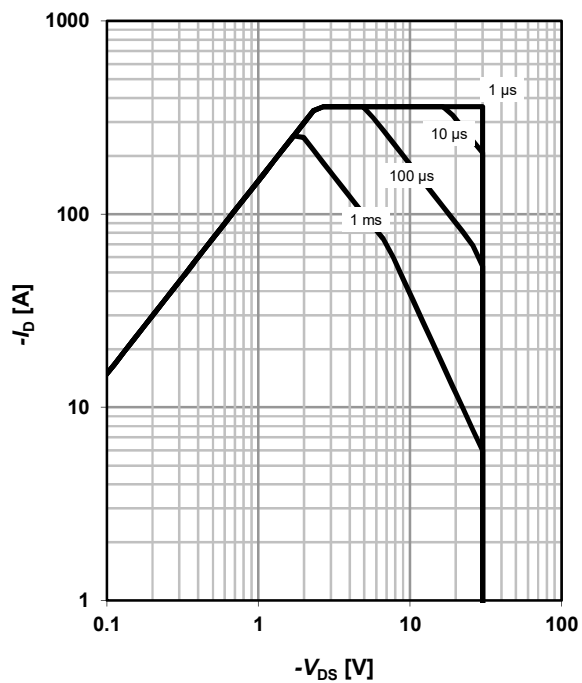
$$I_D = f(T_C); V_{\text{GS}} \leq -6\text{V}$$



### 3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25\text{ °C}; D = 0$$

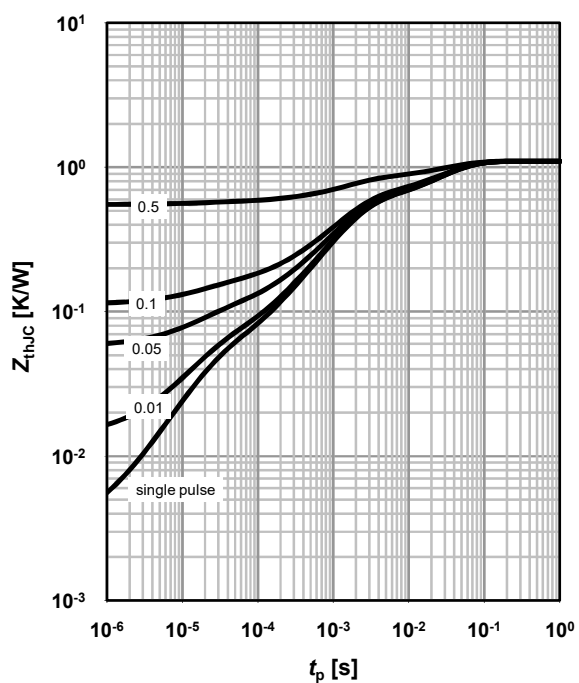
parameter:  $t_p$



### 4 Max. transient thermal impedance

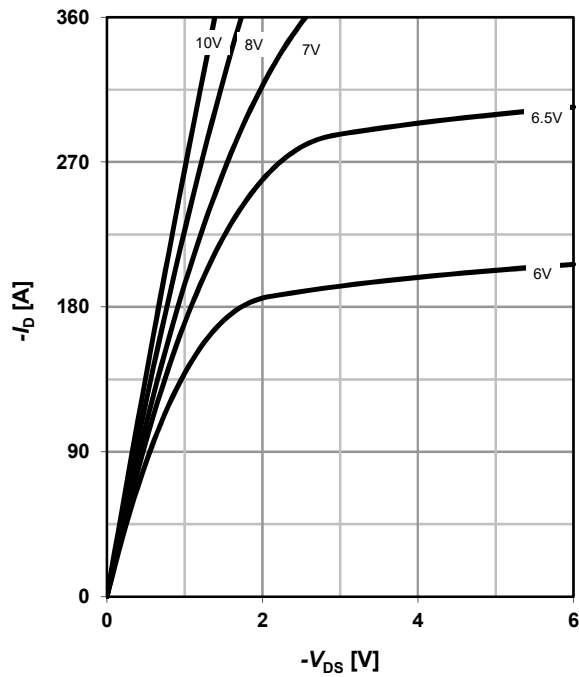
$$Z_{\text{thJC}} = f(t_p)$$

parameter:  $D = t_p/T$



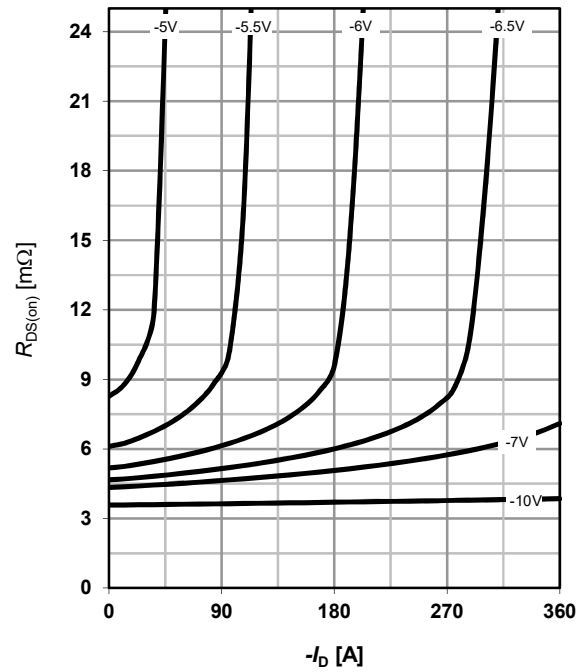
### 5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$ 

parameter:  $V_{GS}$ 


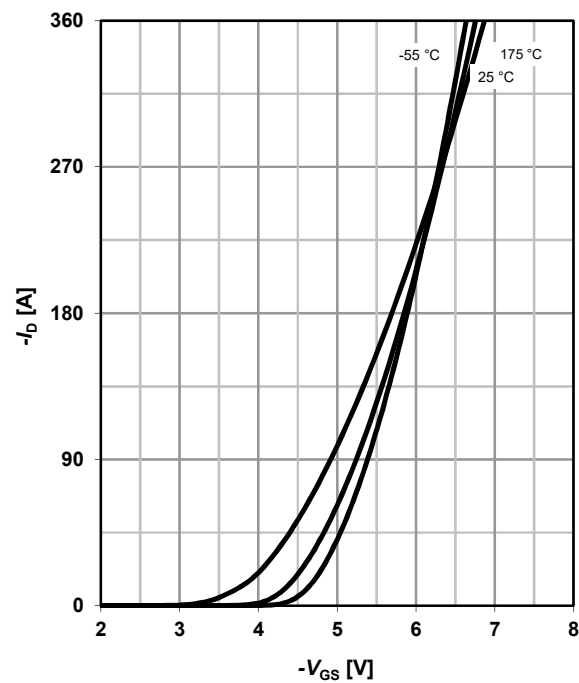
### 6 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$ 

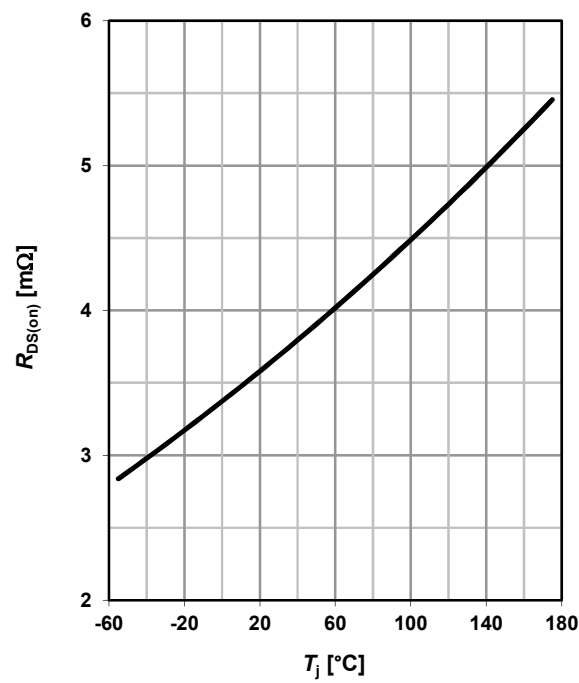
parameter:  $V_{GS}$ 


### 7 Typ. transfer characteristics

 $I_D = f(V_{GS}); V_{DS} = -6V$ 

parameter:  $T_j$ 


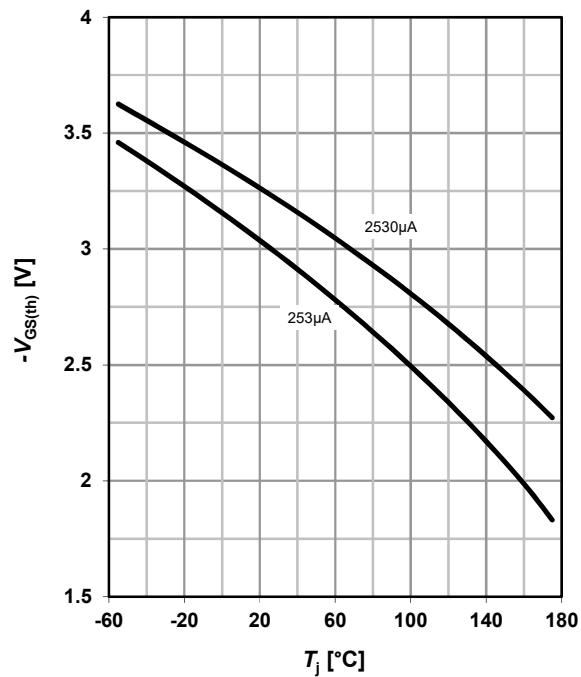
### 8 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(T_j); I_D = -90\text{ A}; V_{GS} = -10\text{ V}$ 


### 9 Typ. gate threshold voltage

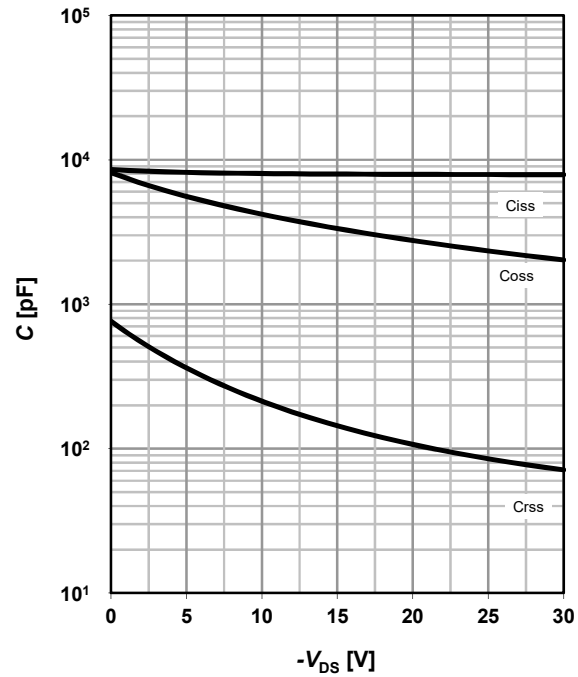
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter:  $-I_D$



### 10 Typ. capacitances

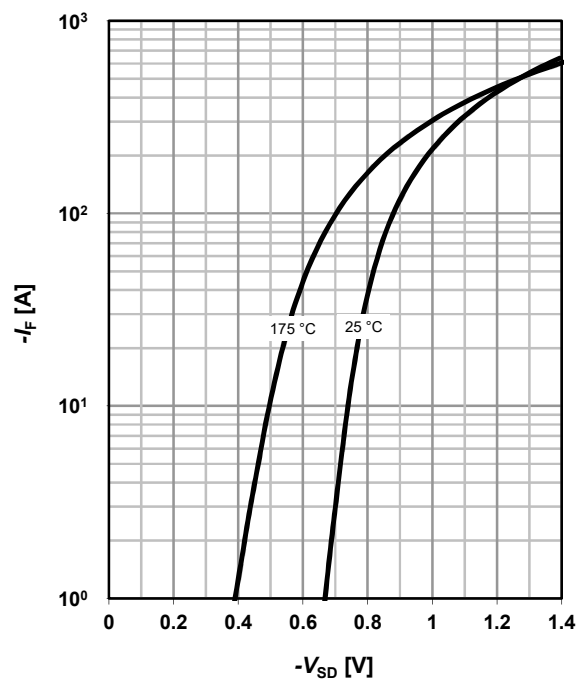
$$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$$



### 11 Typical forward diode characteristics

$$I_F = f(V_{SD})$$

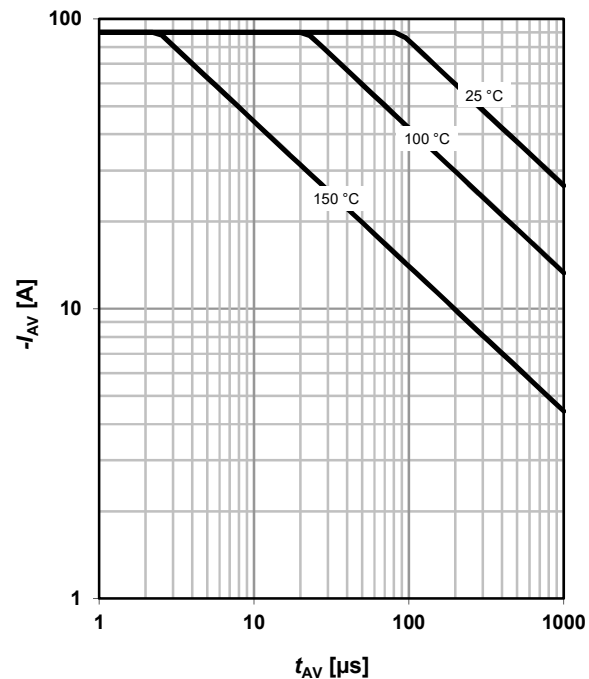
parameter:  $T_j$



### 12 Avalanche characteristics

$$I_{AS} = f(t_{AV})$$

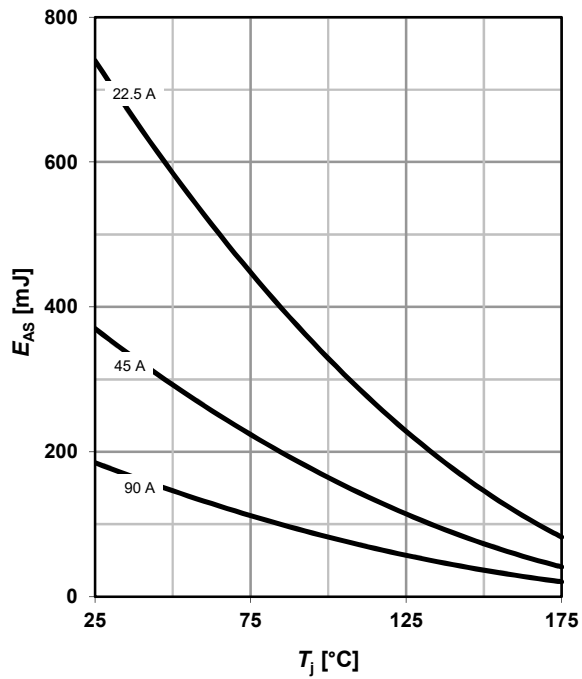
parameter:  $T_{j(start)}$



### 13 Avalanche energy

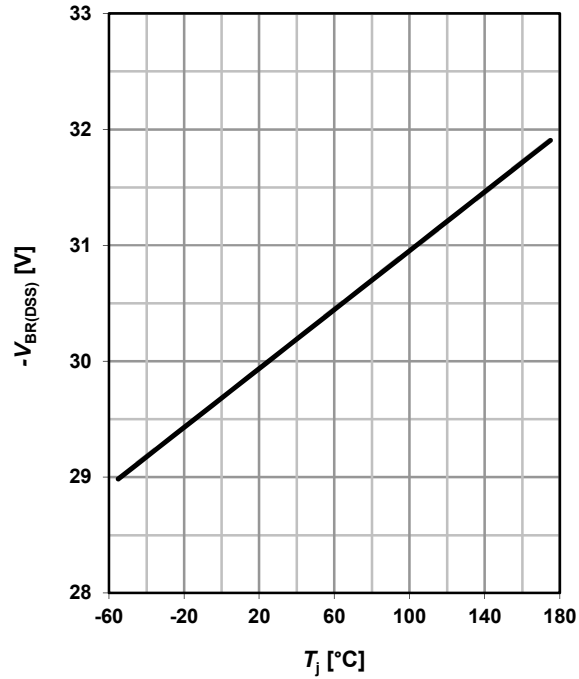
$$E_{AS} = f(T_j)$$

parameter:  $I_D$



### 14 Drain-source breakdown voltage

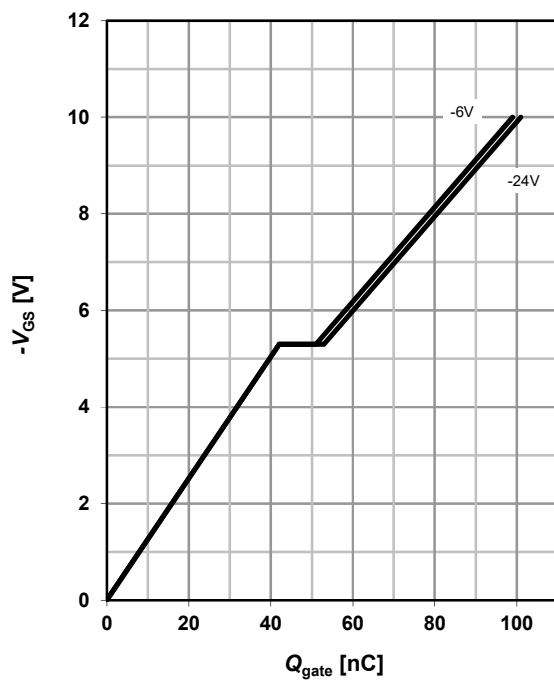
$$V_{BR(DSS)} = f(T_j); I_D = -1 \text{ mA}$$



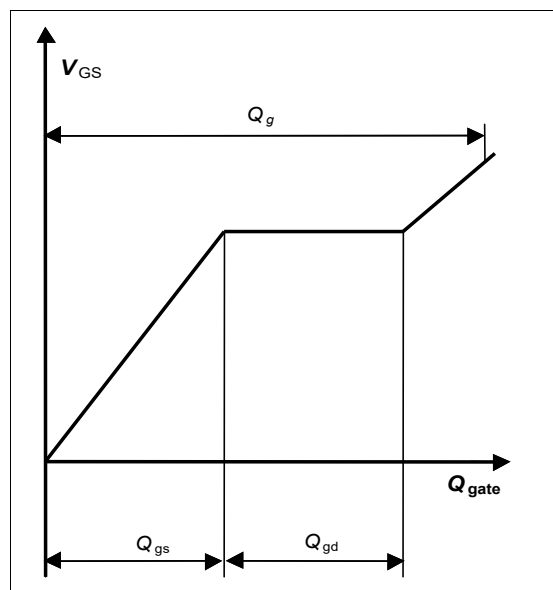
### 15 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = -90 \text{ A pulsed}$$

parameter:  $V_{DD}$



### 16 Gate charge waveforms



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## Revision History

| Version      | Date       | Changes          |
|--------------|------------|------------------|
| Revision 1.0 | 2008-07-30 | Final data sheet |
| Revision 1.1 | 2022-03-14 | Corrected Crss   |

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